

Supplementary Information for:

Dual Ionic Conductivity in $\text{Ba}_3\text{InGa}_2\text{O}_{7.5}$: Correlating Structure and Electrochemical Properties

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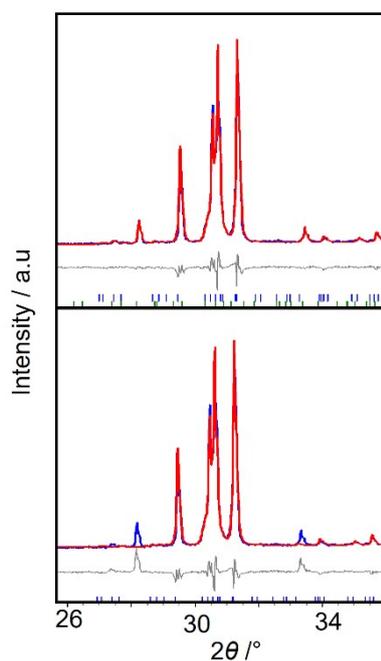


Fig. S1 Partial XRD pattern collected on $\text{Ba}_3\text{InGa}_2\text{O}_{7.5}$ after initial 20-hour synthesis fitted with $P2/c$ model and both with and without BaGa_2O_4 included as a secondary phase. The peaks at ~ 28.0 and 33.2° are also present in the work of Kochetova *et al.*¹

Table S1. Crystallographic data for room temperature Ba₃InGa₂O_{7.5} with unit-cell parameters $a = 7.9557(13)$ Å, b

Atom	Site	x	y	z	Occ.	$B_{\text{iso}} / \text{Å}^2$
Ba1	2e	0	0.267(3)	0.25	1	1.51(3)
Ba2	2f	0.5	0.295(2)	0.25	1	1.51(3)
Ba3	4g	0.0267(6)	0.754(2)	0.0871(3)	1	1.51(3)
Ba4	4g	0.5007(7)	0.246(2)	0.5802(4)	1	1.51(3)
In1	4g	0.2443(7)	0.250(2)	0.4109(4)	0.86(2)	0.67(4)
Ga1	4g	0.2443(7)	0.250(2)	0.4109(4)	0.14(2)	0.67(4)
Ga2	4g	0.244(2)	0.254(3)	0.0595(6)	1	0.67(4)
Ga3	4g	0.223(1)	0.767(3)	0.2699(5)	0.86(2)	0.67(4)
In2	4g	0.223(1)	0.767(3)	0.2699(5)	0.14(2)	0.67(4)
O1	2e	0	0.78(1)	0.25	1	0.2(2)
O2	4g	0.046(4)	0.74(1)	0.604(2)	1	0.2(2)
O3	4g	0.470(4)	0.25(2)	0.092(2)	1	0.2(2)
O4	4g	0.268(4)	0.169(6)	0.293(2)	1	0.2(2)
O5	4g	0.233(6)	0.536(7)	0.337(3)	1	0.2(2)
O6	4g	0.254(6)	0.543(7)	0.491(3)	1	0.2(2)
O7	4g	0.233(5)	0.983(8)	0.004(3)	1	0.2(2)
O8	4g	0.363(4)	0.296(7)	0.691(2)	1	0.2(2)

$= 5.8762(9)$ Å, $c = 18.2237(3)$ Å and $\beta = 91.570(1)^\circ$ in space group $P2/c$.

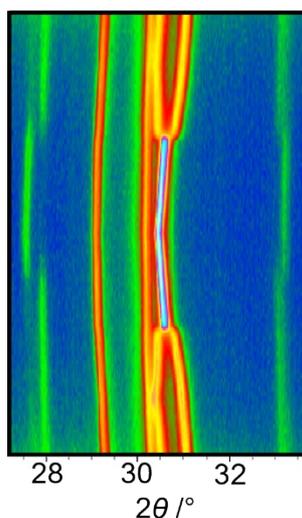


Fig. S2 Expanded view of 30-1000-30 °C VT-PXRD patterns in the 2θ region of ~ 27 - 34° showing the evolution of the 2 wt% BaGa₂O₄ impurity phase with temperature through the peaks at ~ 28.0 and 33.2° .

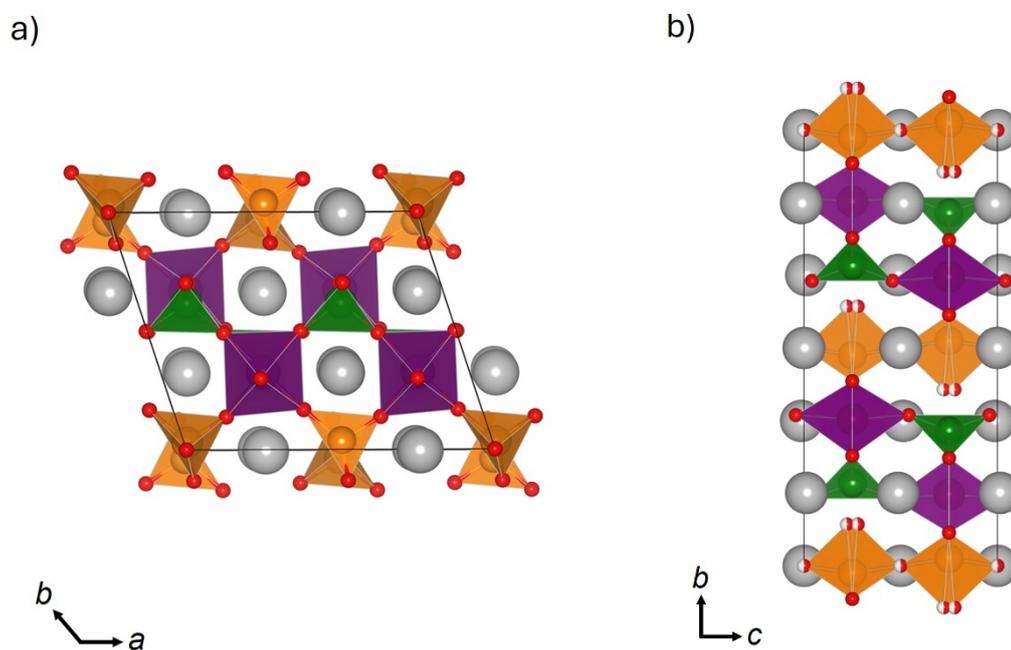


Fig. S3 The potential high temperature structural models. a) The $P2_1/a$ model. b) The final $Cmcm$ model. (A^{2+} in grey, Oh^{3+} in purple, Td^{3+} in green/orange and O^{2-} in red).

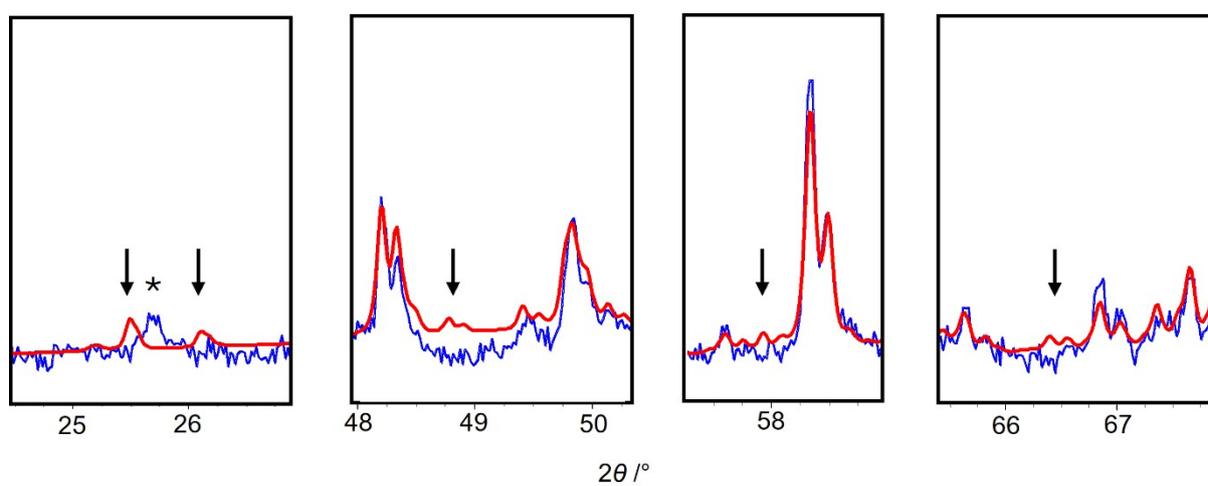


Fig. S4 Example 2θ regions from the Rietveld fit of the $P2_1/a$ model against the high temperature PXRD pattern for $Ba_3InGa_2O_{7.5}$. The peak marked with an ' * ' is a minor impurity peak.

Table S2. Crystallographic data for Ba₃InGa₂O_{7.5} at 1000 °C with unit-cell parameters $a = 5.9251(3)$ Å, $b = 18.4230(7)$ Å, $c = 8.0957(3)$ Å in space group *Cmcm*.

Atom	Site	<i>x</i>	<i>y</i>	<i>z</i>	Occ.	B _{iso} /Å ²
Ba1	4 <i>b</i>	0	0.5	0	1	2.75(7)
Ba2	8 <i>f</i>	0	0.1674(4)	0.0133(5)	1	2.75(7)
In1	4 <i>c</i>	0	0.3364(6)	0.25	0.88(3)	1.2(2)
Ga1	4 <i>c</i>	0	0.3364(6)	0.25	0.12(3)	1.2(2)
Ga2	4 <i>c</i>	0	0.6896(7)	0.25	1	1.0(2)
Ga3	4 <i>c</i>	0	0.9834(7)	0.25	0.88(3)	1.0(2)
In2	4 <i>c</i>	0	0.9834(7)	0.25	0.12(3)	1.0(2)
O1	4 <i>a</i>	0	0	0	0.5	1.5(3)
O2	8 <i>f</i>	0	0.654(2)	0.042(2)	1	1.5(3)
O3	8 <i>g</i>	0.256(7)	0.924(3)	0.25	1	1.5(3)
O4	8 <i>g</i>	0.753(6)	0.753(3)	0.25	1	1.5(3)
O5	8 <i>f</i>	0	0.095(3)	0.278(8)	0.5	1.5(3)

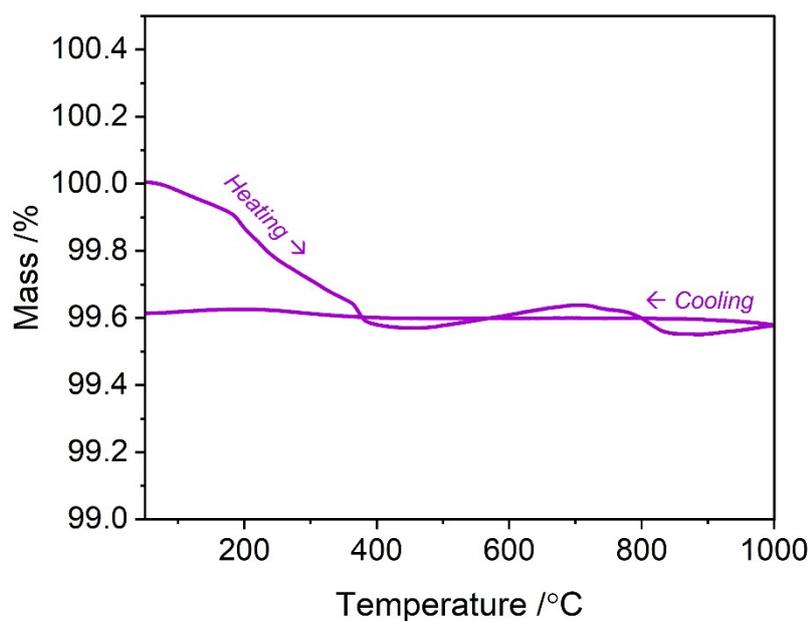


Fig. S5 TGA trace on heating and cooling for Ba₃InGa₂O_{7.5}.

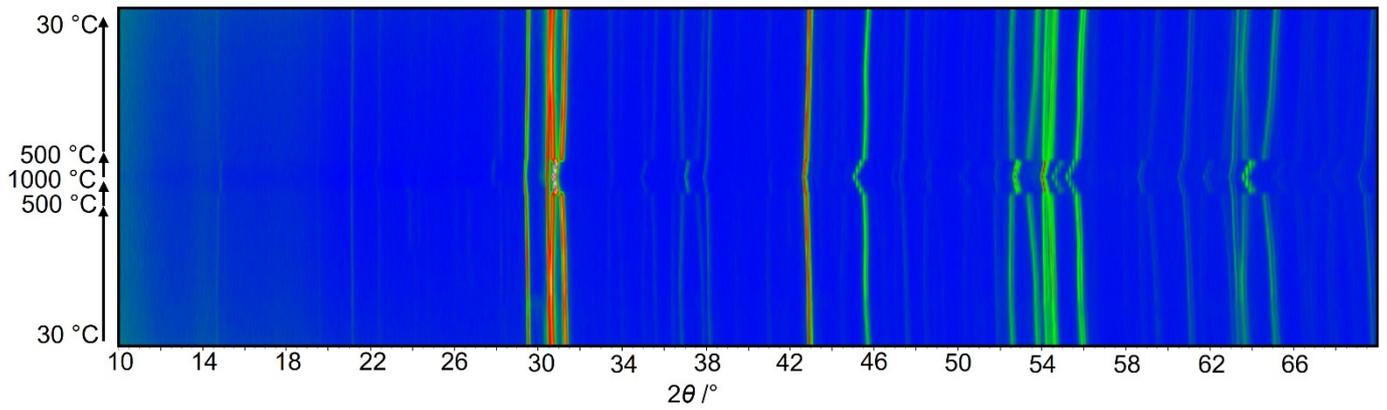


Fig. S6 Powder X-ray diffraction patterns of $\text{Ba}_3\text{InGa}_2\text{O}_{7.5}$, viewed as a colour map where blue and red correspond to regions of low and high intensity, as a function of temperature between 30 and 1000 °C. The limited number of data points above 500 °C is due to larger temperature intervals.

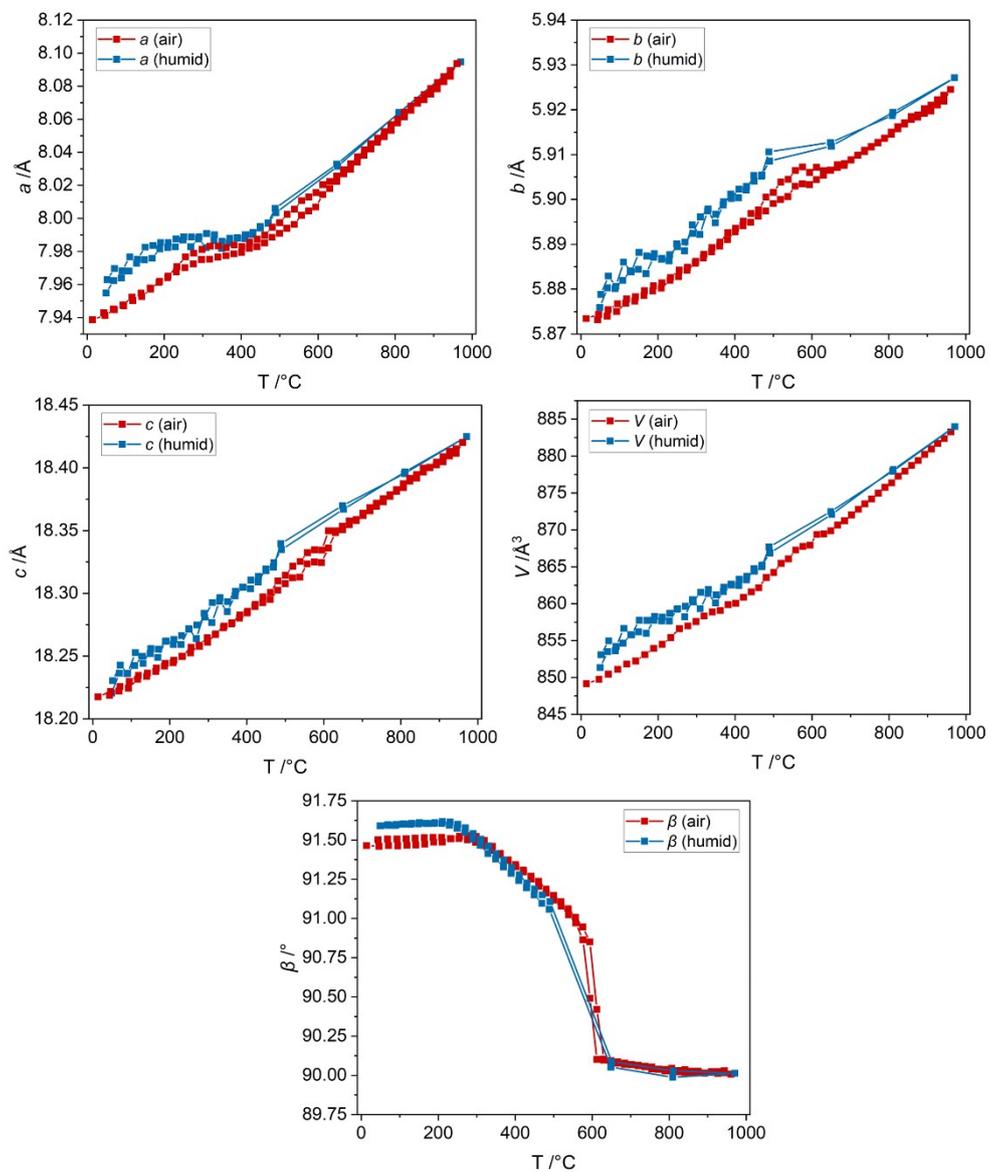


Fig. S7 Extracted unit-cell parameters as a function of temperature under humidified and normal atmospheres.

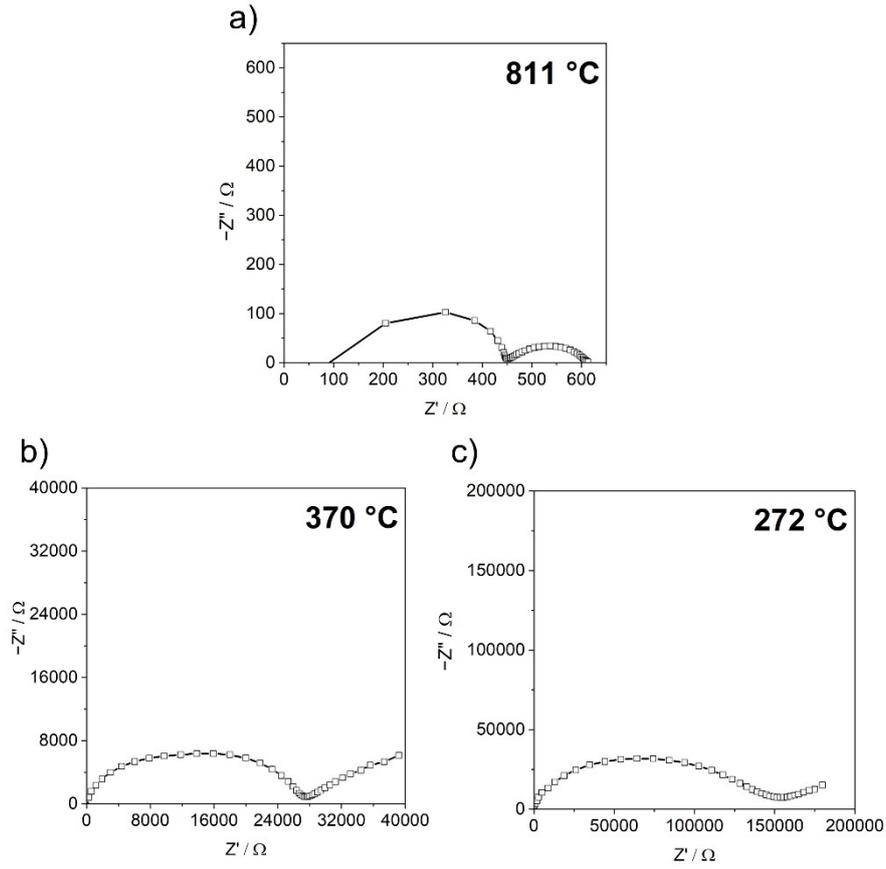


Fig. S8 Complex plane plots at a) 811 °C b) 370 °C and c) 272 °C for $\text{Ba}_3\text{InGa}_2\text{O}_{7.5}$ measured in air.

References

- [1] N. Kochetova, V. Cherepanova, A. Pikalova and A. Gilev, *Chim. Techno Acta*, 2024, **11**, 202411102.